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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

re Patent Application of

SHINGUBARA, S. et al.

Atty. Ref.:

925-287

Serial No.

10/809,681

Group:

1762

Filed:

March 26, 2004

Examiner:

For:

METHOD OF MANUFACTURING MULTILEVEL

INTERCONNECTION

\* \* \* \* \* \* \* \* \*

Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450

Sir:

## INFORMATION DISCLOSURE STATEMENT

As suggested by 37 C.F.R. 1.97, the undersigned attorney brings to the attention of the Patent and Trademark Office the references listed on the attached form PTO-1449.

All listed documents are attached.

This application was filed after June 30, 2003 so that copies of U.S. Patent Publications are not required and are not attached.

Listed foreign patent publications and other documents are enclosed.

The partial translations were provided to the undersigned by the applicants' foreign representative. The undersigned has no knowledge regarding the pertinency of the partially translated portions vis-á-vis the document as a whole. The partial translations are merely provided for whatever convenience they may be.

The listed documents were cited in the ISR and copies should have been supplied by WIPO directly to the US PTO. If copies are not timely received from WIPO, please telephone the undersigned so that copies can be timely supplied for the Examiner's consideration in this US National Phase Application.

This is not to be construed as a representation that a search has been made or that no better prior art exists, or that a reference is relevant merely because cited.

SHINGUBARA, S. et al. Serial No. 10/809,681

The Examiner is requested to initial the attached form PTO-1449 and to return a copy of the initialed document to the undersigned as an indication that the attached references have been considered and made of record.

Respectfully submitted, NIXON & VANDERHYE P.C.

June 22, 2004

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I. Warren Burnam, Jr.

Reg. No. 29,366

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